## ABSTRACT OF THE DISCLOSURE

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A semiconductor photocathode comprises a p<sup>+</sup>-type semiconductor substrate of GaSb, and a p<sup>-</sup>-type light absorbing layer of InAsSb. A p<sup>+</sup>-type hole blocking layer is formed between the substrate and the light absorbing layer having wider energy band gap than that of the light absorbing layer, the blocking layer being made of AlGaSb.